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To Examiner Robert Kunemund - Art Unit 1765
U.S. Patent Office
Washington, DC 20231

Facsimile number 12967-00200001 / (703) 872-9439

From John B. Pegram

Re 'Tomohiro Kawase et al.
S.N. 09/824,965
Our Ref.: 12967-002001

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Message

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Attorney's Docket No.: 12967-002001

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Tomohiro Kawase et al Art Unit : 1765
Serial No. : 09/824,965 Examiner : Robert Kunemund
Filed : April 3, 2001
Title : METHOD OF PREPARING GROUP III-V COMPOUND SEMICONDUCTOR
CRYSTAL

Commissioner for Patents
Washington, D.C. 20231

By Facsimile

PRELIMINARY AMENDMENT

Prior to examination, please amend this reissue application as follows:

In the specification:

Add the following new claims 40 - 66:

40. A method of preparing a carbon-doped group III-V compound semiconductor comprising the steps of:

melting a boron oxide substance in contact with carbon, thereby forming a boron oxide - carbon mixture,

heating and melting a III-V compound semiconductor raw material together with said boron oxide - carbon mixture.

maintaining said compound raw material in melted form for a period to permit carbon to migrate from said boron oxide - carbon mixture into said compound raw material, and

solidifying said melted compound raw material to form a crystalline carbon-doped compound semiconductor.

wherein the amount of carbon in the initial boron oxide - carbon mixture is larger than the amount of carbon doped into said compound semiconductor.

41. The method of preparing a carbon-doped group III-V compound semiconductor according to claim 40, wherein said boron oxide substance comprises boron oxide and water.